

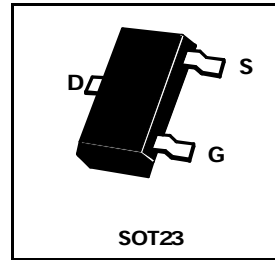
**SOT23 N-CHANNEL ENHANCEMENT  
MODE VERTICAL DMOS FET**

**BS170F**

**ISSUE 3 - JANUARY 1996**

**FEATURES**

- \* 60Volt  $V_{DS}$
- \*  $R_{DS(ON)} = 5\Omega$



PARTMARKING DETAIL - MV

**ABSOLUTE MAXIMUM RATINGS.**

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	$V_{DS}$	60	V
Continuous Drain Current at $T_{amb}=25^{\circ}C$	$I_D$	0.15	mA
Pulsed Drain Current	$I_{DM}$	3	A
Gate Source Voltage	$V_{GS}$	$\pm 20$	V
Power Dissipation at $T_{amb}=25^{\circ}C$	$P_{tot}$	330	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

**ELECTRICAL CHARACTERISTICS (at  $T_{amb} = 25^{\circ}C$  unless otherwise stated).**

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	$BV_{DSS}$	60	90		V	$I_D=100\mu A, V_{GS}=0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	0.8		3	V	$I_D=1mA, V_{DS}=V_{GS}$
Gate-Body Leakage	$I_{GSS}$			10	nA	$V_{GS}=15V, V_{DS}=0V$
Zero Gate Voltage Drain Current	$I_{DSS}$			0.5	$\mu A$	$V_{DS}=25V, V_{GS}=0V$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$			5	$\Omega$	$V_{GS}=10V, I_D=200mA$
Forward Transconductance (1)(2)	$g_{fs}$		200		mS	$V_{DS}=10V, I_D=200mA$
Input Capacitance (2)	$C_{iss}$		60		pF	$V_{DS}=10V, V_{GS}=0V, f=1MHz$
Turn-On Delay Time (2)(3)	$t_{d(on)}$			10	ns	$V_{DD}\approx -15V, I_D=600mA$
Turn-Off Delay Time (2)(3)	$t_{d(off)}$			10	ns	

(1) Measured under pulsed conditions. Width=300 $\mu s$ . Duty cycle  $\leq 2\%$  (2) Sample test.

(3) Switching times measured with 50 $\Omega$  source impedance and <5ns rise time on a pulse generator

Spice parameter data is available upon request for this device

For typical characteristics graphs refer to ZVN3306F datasheet.